

[METHOD OF FABRICATING A POLYSILICON THIN FILM]

Abstract

The present invention uses higher protrusions of an initially formed silicon layer as crystalline seeds in the subsequent crystallization step so that the newly-formed polysilicon thin film has smoother and bigger silicon grains, and has lesser density of protrusions. Furthermore, the polysilicon thin film of the present invention can be applied to form polysilicon thin film transistors or other devices.